UNISONIC TECHNOLOGIES CO., LTD

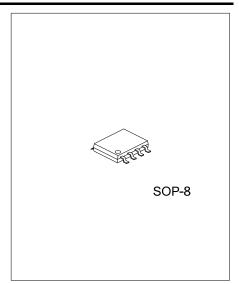
UT4410 Power MOSFET

N-CHANNEL 30-V (D-S) MOSFET

DESCRIPTION

As advanced N-channel logic level enhancement MOSFET, the UT4410 is produced using UTC's high cell density, DMOS trench technology, which has been specially tailored to minimize the on-resistance and maintain low gate charge for superior switching performance.

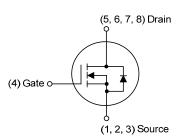
These devices can be particularly suited for such low voltage applications: cellular phone and notebook computer power management and other battery powered circuits where high-side switching and low in-line power loss are needed in a very small outline surface mount package.



FEATURES

- * $R_{DS(ON)}$ < 18 m Ω @ V_{GS} =10V, I_{D} =10A
- * $R_{DS(ON)}$ < 20 m Ω @ V_{GS} =4.5V, I_{D} =8A
- * Ultra low gate charge (typical 11 nC)
- * Low reverse transfer capacitance (C_{RSS} = typical 35 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



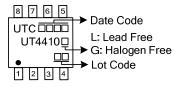
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment							Dooking	
Lead Free	Halogen Free	Package	1	2	3	4	5	6	7	8	Packing
UT4410L-S08-R	UT4410G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain



MARKING



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ABSOLUTE MAXIMUM RATINGS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	30	٧
Gate-Source Voltage	V_{GSS}	±20	٧
Continuous Drain Current	I _D	11.6	Α
Pulsed Drain Current	I _{DM}	46.4	Α
Power Dissipation	P_{D}	3.6	W
Junction Temperature	TJ	-55 ~ + 150	Ĵ

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	60	°C/W

Note: The device mounted on 1in² FR4 board with 2 oz copper

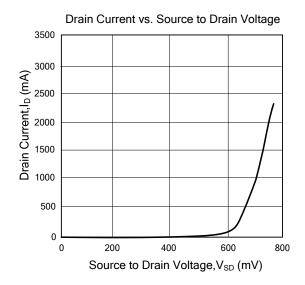
ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	1			μΑ
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nΑ
ON CHARACTERISTICS						
Gate-Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1.0		3.0	V
Static Drain, Source On Registance(Note)	R _{DS(ON)}	V_{GS} =10V, I_D =10A		12	18	mΩ
Static Drain–Source On–Resistance(Note)		V _{GS} =4.5V, I _D =8A		17	20	11122
On-State Drain Current(Note)	$I_{D(ON)}$	V _{DS} = 5V, V _{GS} =10V	20			Α
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			700	800	pF
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V, f=1.0MHz		120		pF
Reverse Transfer Capacitance	C _{RSS}			35		pF
Gate Resistance	R_G	V_{DS} =0V, V_{GS} =0V, f=1.0MHz		0.9		Ω
SWITCHING PARAMETERS						
Turn-ON Delay Time	t _{D(ON)}			14	32	ns
Turn-ON Rise Time	t _R	V_{DD} =25V, I_D =1A, R_L =25 Ω		12	64	ns
Turn-OFF Delay Time	t _{D(OFF)}	V_{GEN} =10V, R_{G} =6 Ω		43	280	ns
Turn-OFF Fall-Time	t _F			4	192	ns
Total Gate Charge	Q_G	V _{DS} =15V, V _{GS} =4.5V, I _D =10A		11	15	nC
Total Gate Charge	Q_GT			20	26	nC
Gate Source Charge	Q_GS	V_{DS} =15V, V_{GS} =10V, I_{D} =10A		5		nC
Gate Drain Charge	Q_GD			4.9		nC
SOURCE- DRAIN DIODE RATINGS AND C	HARACTER	ISTICS		,	1	
Drain-Source Diode Forward Voltage	V_{SD}	I _S =2.3 A,V _{GS} =0V		0.7	1.1	V

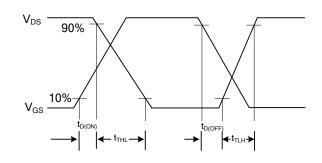
Note: Pulse test; pulse width ≤ 300us, duty cycle≤ 2%

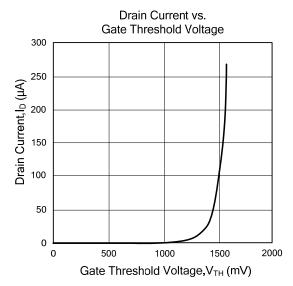


TYPICAL CHARACTERISTICS

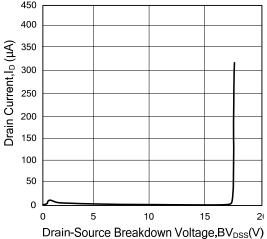


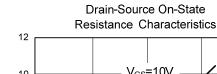
Switching Time Waveforms

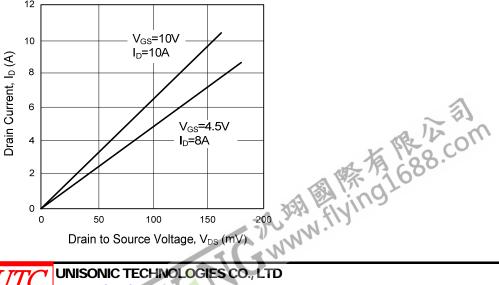




Drain Current vs. Drain-Source Breakdown Voltage 450







Drain to Source Voltage, V_{DS} (mV)

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